L Number	Hits		DB	Time stamp
-	21	"3943462"	USPAT;	2002/08/30 15:08
			US-PGPUB;	
i i			EPO; JPO;	
1			DERWENT;	
_	0	(semiconductor adj laser) and facet and	IBM_TDB	0000 (00 (00 15 15
-	U	(anti\$reflection adj coating) and	USPAT;	2002/08/30 15:17
		(thickness adj3 quarter) and sion\$h and	US-PGPUB; EPO; JPO;	
		pecvd and (optical adj index)	DERWENT;	
		recta dia (optioni da) indon,	IBM TDB	
-	0	(semiconductor adj laser) and facet and	USPAT;	2002/08/30 15:15
1		(antireflection adj coating) and	US-PGPUB;	
		(thickness adj3 quarter) and sion\$h and	EPO; JPO;	
		pecvd and (optical adj index)	DERWENT;	
.			IBM_TDB	
-	0	, , , , , , , , , , , , , , , , , , , ,	USPAT;	2002/08/30 15:16
		(reflection adj coating) and (thickness	US-PGPUB;	
		adj3 quarter) and sion\$h and pecvd and (optical adj index)	EPO; JPO;	
		(optical adj index)	DERWENT; IBM TDB	
_	0	(semiconductor adj laser) and facet and	USPAT;	2002/08/30 15:16
	9	(reflection adj coating) and (thickness	US-PGPUB;	2002/00/30 13:10
		adj3 quarter) and pecvd and (optical adj	EPO; JPO;	
		index)	DERWENT;	
			IBM TDB	
-	0	(semiconductor adj laser) and facet and	USPAT;	2002/08/30 15:16
		(reflection adj coating) and (thickness	US-PGPUB;	
		adj3 quarter) and pecvd	EPO; JPO;	
			DERWENT;	
	0]	IBM_TDB	0000 100 100 15 15
-	0	1 (USPAT;	2002/08/30 15:17
		coating) and (thickness adj3 quarter) and sion\$h and pecvd and (optical adj index)	US-PGPUB;	İ
		stonan and pecva and (optical adj index)	EPO; JPO; DERWENT;	1
			IBM TDB	
_	6	(semiconductor adj laser) and facet and	USPAT;	2002/08/30 15:29
	Ū	(reflection adj coating) and (thickness	US-PGPUB;	2002,00,30 13.23
		adj3 quarter)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	(semiconductor adj laser) and (reflection	USPAT;	2002/08/30 15:30
		adj coating) and ((pecvd) or (plasma adj	US-PGPUB;	
		enhanced)) and sixoynyh	EPO; JPO;	
			DERWENT;	i
	0	(semiconductor adj laser) and (reflection	USPAT;	2002/08/30 15:30
	١	adj coating) and ((pecvd) or (plasma adj	US-PGPUB;	2002/00/30 13:30
		enhanced)) and sixoyny	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	0	(semiconductor adj laser) and (reflection	USPAT;	2002/08/30 15:31
		adj coating) and ((pecvd) or (plasma adj	US-PGPUB;	
		enhanced)) and sion	EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/05/55
-	13	(semiconductor adj laser) and (reflection	USPAT;	2002/08/30 16:28
	}	<pre>adj coating) and ((pecvd) or (plasma adj enhanced))</pre>	US-PGPUB;	
	İ	emianced))	EPO; JPO; DERWENT;	
			IBM TDB	
_	0	(semiconductor adj laser) and (reflection	USPAT;	2002/08/30 15:32
	Ĭ	adj coating) and ((pecvd) or (plasma adj	US-PGPUB;	-552, 55, 55 15.52
		enhanced))and (optical adj index)	EPO; JPO;	
			DERWENT;	
		·	IBM_TDB	
-	4	silicon near3 oxide near nitride near3	USPĀT;	2002/09/01 11:47
		hydrogen and reflection and coating	US-PGPUB;	
	İ		EPO; JPO;	,
			DERWENT;	
			IBM_TDB	

_	116	(semiconductor adj laser) and coating and	USPAT;	2002/09/01 11:49
	110	(reflectiv\$3 adi3 index)	1	2002/09/01 11:49
1		(Terrectives adjoinidex)	US-PGPUB;	
i			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1	(semiconductor adj laser) and coating and	USPAT;	2002/09/01 11:52
		(reflectiv\$3 adj3 index) and 1.83	US-PGPUB;	
		;	EPO; JPO;	
		,	DERWENT;	
			IBM_TDB	
-	8	(semiconductor adj laser) and coating and	USPAT;	2002/09/01 12:25
		(reflectiv\$3 adj3 index) and (standing adj	US-PGPUB;	
		wave)	EPO; JPO;	0/1
			DERWENT;	
			IBM TDB	
-	114	(semiconductor adj laser) and (coating	USPAT;	2002/09/01 13:20
	-	adj3 index)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	1 1		IBM TDB	
] -	65	(semiconductor adj laser) and (reflection	USPAT;	2002/09/01 13:22
		adj coating) and (quarter adj wavelength)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	1		IBM TDB	
_	34	(semiconductor adj laser) and (reflection	USPAT;	2002/09/01 13:22
		adj coating) and (quarter adj wavelength)	US-PGPUB;	
		and gaas	EPO; JPO;	
		3	DERWENT;	
			IBM TDB	
			100	

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